

# TXG8041-EP Enhanced Product 4-bit, ±80V Ground-Level Translator

#### 1 Features

- Supports DC shifts up to ±80V
- AC Noise Rejection of 140V<sub>PP</sub> up to 1MHz
- CMTI of 250V/µs
- Low Prop Delay (<5ns) and Ch-Ch Skew (0.35ns)</li>
- Greater than 250Mbps
- Low power consumption (0.65mA per channel at 1Mbps, 1.8V)
- Fully configurable dual-rail design allows each port to operate from 1.71V to 5.5V
- Supports V<sub>CC</sub> disconnect feature (I/Os are forced into high-Z)
- Schmitt-trigger inputs allows for slow and noisy signals
- Inputs with integrated static pull-down resistors prevent channels from floating
- Operating temperature from –40°C to +125°C
- Latch-up performance exceeds 100mA per JESD 78, class II
  - ESD protection exceeds JESD 22
  - 4000V human-body model
  - 500V charged-device model
- Small SOT-24 (DYY-14) package

# 2 Applications

- · Aircraft cockpit display
- Flight control unit
- Radar
- Sonar
- · Electronic warfare
- · Seeker front end

#### 3 Description

The TXG8041-EP is a 4-bit, fixed direction, non-galvanic based voltage and ground-level translator that can support both logic-level shifting between 1.71V to 5.5V and ground-level shifting up to ±80V. Compared to traditional level shifters, the TXG8041-EP can solve the challenges of voltage translation across different ground levels. The Simplified Diagram shows a common use case where DC shift occurs between GNDA to GNDB due to parasitic resistance or capacitance.

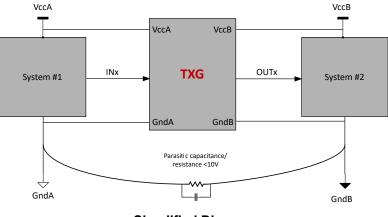
 $V_{\rm CCA}$  is referenced to GNDA and  $V_{\rm CCB}$  is referenced to GNDB. Ax pins are referenced to  $V_{\rm CCA}$  logic level while Bx pins are referenced to  $V_{\rm CCB}$  logic levels. Both A port and B port can accept voltages from 1.71V to 5.5V. This device includes two enable pins that can place the respective outputs in a high-impedance state when the OE pin is connected to GND or left floating. In the event of input power or signal loss, the output is default low when OE is High (refer to Table 7-1). The leakage between GNDA and GNDB is 45nA when  $V_{\rm CC}$  to GND is shorted.

The TXG8041-EP helps improve noise immunity and power sequencing across different ground domains, while providing low power consumption, latency and channel-to-channel skew. TXG8041-EP can supress noise levels of 160V<sub>PP</sub> up to 1MHz (Figure 7-3). This device can support multiple interfaces such as SPI, UART, GPIO, and I2S.

#### **Package Information**

PART NUMBER TXG8041-EP	PACKAGE (1)	BODY SIZE (NOM)
TXG8041-EP	DYY (SOT-14)	4.20mm × 2.00mm

 For all available packages, see the orderable addendum at the end of the data sheet.



**Simplified Diagram** 



# **Table of Contents**

1 Features	7.2 Functional Block Diagram	.17
2 Applications	7.3 Feature Description	
3 Description1	7.4 Device Functional Modes	
4 Pin Configuration and Functions3	8 Application and Implementation	.22
5 Specifications4	8.1 Application Information	22
5.1 Absolute Maximum Ratings4	8.2 Typical Application	
5.2 ESD Ratings4	8.3 Power Supply Recommendations	
5.3 Recommended Operating Conditions5	8.4 Layout	
5.4 Thermal Information5	9 Device and Documentation Support	
5.5 Electrical Characteristics6	9.1 Device Support	25
5.6 Switching Characteristics, V <sub>CCA</sub> = 1.8 ± 0.15V9	9.2 Documentation Support	25
5.7 Switching Characteristics, V <sub>CCA</sub> = 2.5 ± 0.2V9	9.3 Receiving Notification of Documentation Updates	.25
5.8 Switching Characteristics, V <sub>CCA</sub> = 3.3 ± 0.3V 10	9.4 Support Resources	
5.9 Switching Characteristics, V <sub>CCA</sub> = 5.0 ± 0.5V 11	9.5 Trademarks	.25
5.10 Switching Characteristics: T <sub>sk</sub> , T <sub>MAX</sub> 12	9.6 Electrostatic Discharge Caution	.25
5.11 Typical Characteristics14	9.7 Glossary	
6 Parameter Measurement Information15	10 Revision History	
6.1 Load Circuit and Voltage Waveforms15	11 Mechanical, Packaging, and Orderable	
7 Detailed Description17	Information	25
7.1 Overview17		



# 4 Pin Configuration and Functions

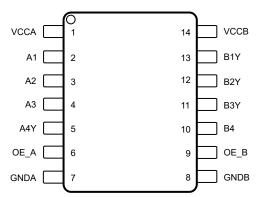


Figure 4-1. TXG8041-EP DYY 14-Pin SOT Top View

**Table 4-1. Pin Functions** 

PI	IN	1/0	DECODINE						
Name	NO.	I/O	DESCRIPTION						
A1	2	I	Input A1. Referenced to V <sub>CCA</sub>						
A2	3	I	Input A2. Referenced to V <sub>CCA</sub>						
A3	4	I	Input A3. Referenced to V <sub>CCA</sub>						
A4Y 5		0	Output A4. Referenced to V <sub>CCA</sub>						
B1Y 13		0	Output B1. Referenced to V <sub>CCB</sub>						
B2Y 12		0	Output B2. Referenced to V <sub>CCB</sub>						
B3Y	11	0	Output B3. Referenced to V <sub>CCB</sub>						
B4	10	I	Input B4. Referenced to V <sub>CCB</sub>						
OE_A	6	I	Active-High Output Enable (A side). Pull to GND to place all outputs in high-impedance mode.						
OE_B	9	I	Active-High Output Enable (B side). Pull to GND to place all outputs in high-impedance mode.						
V <sub>CCA</sub>	1	_	A side supply voltage. 1.71V ≤ V <sub>CCA</sub> ≤ 5.5V						
V <sub>CCB</sub>	14	_	B side supply voltage. 1.71V ≤ V <sub>CCB</sub> ≤ 5.5V						
GNDA	7	_	Ground reference for V <sub>CCA</sub>						
GNDB	8	_	Ground reference for V <sub>CCB</sub>						



## **5 Specifications**

### 5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V <sub>CCA</sub> to V <sub>GNDA</sub>	Supply voltage A to Ground voltage A		-0.5	6.5	V
V <sub>CCB</sub> to V <sub>GNDB</sub>	Supply voltage B to Ground voltage B		-0.5	6.5	V
V <sub>GNDA</sub> to V <sub>GNDB</sub>	Ground voltage B to Ground voltage A		-82	82	V
		I/O Ports (A Port) to V <sub>GNDA</sub>	-0.5	6.5	V
V <sub>I</sub>	Input Voltage <sup>(2)</sup>	I/O Ports (B Port) to V <sub>GNDB</sub>	-0.5	6.5	
		OE	-0.5	6.5	V
V	Voltage applied to any output in the high-	A Port to V <sub>GNDA</sub>	-0.5	6.5	V
Vo	impedance or power-off state <sup>(2)</sup>	B Port to V <sub>GNDB</sub>	-0.5	6.5	
V	Voltage applied to any output in the high or low	A Port to V <sub>GNDA</sub>	-0.5	6.5	V
Vo	state <sup>(2)</sup> (3)	B Port to V <sub>GNDB</sub>	-0.5	6.5	
I <sub>IK</sub>	Input clamp current	V <sub>1</sub> < 0	-20		mA
I <sub>OK</sub>	Output clamp current	V <sub>O</sub> < 0	-20		mA
Io	Continuous output current		-16	16	mA
	Continuous current through V <sub>CC</sub> or GND	-64	64	mA	
T <sub>j</sub>	Junction Temperature			150	°C
T <sub>stg</sub>	Storage temperature		-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under <u>Section 5.1</u> may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under <u>Section 5.3</u> Exposure beyond the limits listed in <u>Section 5.3</u> may affect device reliability.

- (2) The input voltage and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
- 3) The output positive-voltage rating may be exceeded up to 6.5V maximum if the output current rating is observed.

#### 5.2 ESD Ratings

			VALUE	UNIT
V <sub>(ESD)</sub>	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±4000	V
	Electrostatic discharge	Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002 <sup>(2)</sup>	2 <sup>(2)</sup> ±500	

- (1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.



## **5.3 Recommended Operating Conditions**

over operating free-air temperature range (unless otherwise noted) (1) (2) (3)

			MIN	TYP MAX	UNIT
V <sub>CCA</sub>	Supply voltage A - Relative to GNDA		1.71	5.5	V
V <sub>CCB</sub>	Supply voltage B - Relative to GNDB		1.71	5.5	V
V <sub>GNDA</sub> - V <sub>GNDB</sub>	Voltage Between GNDA and GNDB		-80	80	V
		V <sub>CCO</sub> = 1.71V	-4.5		
	High-level output current	V <sub>CCO</sub> = 2.3V	-8		^
Іон		V <sub>CCO</sub> = 3V	-10		mA
		V <sub>CCO</sub> = 4.5V	-12		1
		V <sub>CCO</sub> = 1.71V		4.5	
	I am land autout amont	V <sub>CCO</sub> = 2.3V		8	
I <sub>OL</sub>	Low-level output current	V <sub>CCO</sub> = 3V		10	mA
		V <sub>CCO</sub> = 4.5V		12	1
VI	Input voltage - Relative to GNDA		0	5.5	V
Vo	Output voltage - Relative to GNDB		0	V <sub>cco</sub>	V
T <sub>A</sub>	Operating free-air temperature		-55	150	°C

- (1) V<sub>CCI</sub> is the V<sub>CC</sub> associated with the input port.
- (2)  $V_{CCO}$  is the  $V_{CC}$  associated with the output port.
- (3) All control inputs and data I/Os of this device have weak pulldowns to ensure the line is not floating when undefined external to the device. The input leakage from these weak pulldowns is defined by the I<sub>I</sub> specification indicated under Section 5.5.

### **5.4 Thermal Information**

	THERMAL METRIC <sup>(1)</sup>	TXG8041-EP  DYY (SOT)  14 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	128.4	°C/W
R <sub>0</sub> JC(top)	Junction-to-case (top) thermal resistance	52.4	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	58.5	°C/W
Y <sub>JT</sub>	Junction-to-top characterization parameter	2.7	°C/W
Y <sub>JB</sub>	Junction-to-board characterization parameter	51.9	°C/W

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application note.



# **5.5 Electrical Characteristics**

over operating free-air temperature range (unless otherwise noted) $^{(1)}$   $^{(2)}$ 

						ting free-air erature (T <sub>A</sub> )			
	PARAMETER	TEST CONDITIONS	V <sub>CCA</sub>	V <sub>CCB</sub>	-55°C		UNIT		
					MIN TYP MAX				
		I <sub>OH</sub> = -4.5mA	1.71V	1.71V	1.5				
.,	High-level output	$I_{OH} = -8mA$	2.3V	2.3V	2			V	
V <sub>OH</sub>	voltage (3)	I <sub>OH</sub> = -10mA	3V	3V	2.6			V	
		I <sub>OH</sub> = -12mA	4.5V	4.5V	4				
		I <sub>OL</sub> = 4.5mA	1.71V	1.71V		(	.18		
. ,	Low-level output	I <sub>OL</sub> = 8mA	2.3V	2.3V		(	.33		
V <sub>OL</sub>	voltage <sup>(4)</sup>	I <sub>OL</sub> = 10mA	3V	3V		(	.41	V	
		I <sub>OL</sub> = 12mA	4.5V	4.5V		(	.49		
			1.71V	1.71V		•	.14		
	Positive-going	Data Inputs	2.3V	2.3V		,	.42		
$V_{T+}$	input-threshold	(Ax, Bx)	3V	3V		,	.74	V	
	voltage	(Referenced to V <sub>CCI</sub> )	4.5V	4.5V		2	.47		
			5.5V	5.5V		2	.97		
			1.71V	1.71V		•	.12		
$V_{T+}$	Positive-going input-threshold	OE (Referenced to V <sub>CCA</sub> or V <sub>CCB)</sub>	2.3V	2.3V			.42		
			3V	3V		•	.73	V	
	voltage		4.5V	4.5V		2	.47		
			5.5V	5.5V		2	.94		
			1.71V	1.71V	0.52				
	Negative-going	Data Inputs (Ax, Bx) (Referenced to V <sub>CCI</sub> )	2.3V	2.3V	0.76	-		٧	
V <sub>T-</sub>	input-threshold voltage		3V	3V	1.09				
			4.5V	4.5V	1.77				
			5.5V	5.5V	2.28				
			1.71V	1.71V	0.46				
	Negative-going		2.3V	2.3V	0.76	-		V	
V <sub>T-</sub>	input-threshold	OE (Defendance data)/	3V	3V	1.04				
	voltage	(Referenced to V <sub>CCA</sub> or V <sub>CCB)</sub>	4.5V	4.5V	1.86				
			5.5V	5.5V	2.5				
			1.71V	1.71V	0.24	(	.54		
	Input-threshold	Data Inputs	2.3V	2.3V	0.29	-	0.6		
$\Delta V_{T}$	hysteresis	(Ax, Bx)	3V	3V	0.33	(	.54	V	
	$(V_{T+}-V_{T-})$	(Referenced to V <sub>CCI</sub> )	4.5V	4.5V	0.38	(	.82		
			5.5V	5.5V	0.37	(	.96		
			1.71V	1.71V	0.24	(	.45		
	Input-threshold		2.3V	2.3V	0.28	(	.58		
$\Delta V_{T}$	hysteresis	OE (Peferenced to )/ or )/	3V	3V	0.32	(	.54	V	
	$(V_{T+}-V_{T-})$	(Referenced to V <sub>CCA</sub> or V <sub>CCB)</sub>	4.5V	4.5V	0.35		.58		
			5.5V	5.5V	0.39		.62		
I <sub>I</sub>	Input leakage current	Data Inputs (Ax, Bx) V <sub>I</sub> = V <sub>CCI</sub> or GND	1.71V – 5.5V	1.71V – 5.5V			1.6	μA	



over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup> (2)

					Operatempe			
P	ARAMETER	TEST CONDITIONS	V <sub>CCA</sub>	V <sub>CCB</sub>	-55°C	UNIT		
					MIN	TYP	MAX	
	Floating supply	A Port or B Port	Floating <sup>(5)</sup>	0V - 5.5V	-2.5		2.5	
I <sub>off-float</sub>	Partial power down current	V <sub>I</sub> = GND	0V - 5.5V	Floating <sup>(5)</sup>	-2.5		2.5	μA
I <sub>O</sub>	Tri-state output Output current	A or B Port: V <sub>I</sub> = V <sub>CCA</sub> or V <sub>GNDA</sub> OE = GND	1.71V – 5.5V	1.1V – 5.5V	-5		5	μΑ
Ci	Control Input Capacitance	V <sub>I</sub> = 3.3V or V <sub>GNDA</sub>	3.3V	3.3V		2		pF
C <sub>io</sub>	Data I/O Capacitance	OE = GND, V <sub>O</sub> = 1.71V DC +1MHz -16dBm sine wave	3.3V	3.3V		5		pF
$C_GND$	Cap between grounds	All channels combined (V <sub>CC</sub> both sides are powered on)					49	pF
	grounds	All channels combined (V <sub>CC</sub> to GND shorted)					54	pF
		All channels combined (V <sub>CC</sub> both sides are powered on and inputs are all low)	1.71V – 5.5V	1.71V – 5.5V		45		μΑ
Leakage	Current Leakage between GndA to GndB	All channels combined (V <sub>CC</sub> both sides are powered on and inputs are all high)	1.71V – 5.5V	1.71V – 5.5V		45		μΑ
		All channels combined (V <sub>CC</sub> to GND shorted)	1.71V – 5.5V	1.71V – 5.5V		33		μΑ
CMTI	Common Mode Transient Immunity	Input toggling at 100Mbps Ground shift up to 80V	1.71V – 5.5V	1.71V – 5.5V			1	V/µs
		V V OND	1.71V – 5.5V	1.71V – 5.5V	546		1220	
	V <sub>CCA</sub> supply current	$V_I = V_{CCI}$ or GND $I_O = 0$	0V	5.5V	-3		13	
I <sub>CCA</sub>			5.5V	0V	509		1050	μA
		$V_I = GND$ $I_O = 0$	5.5 V	Floating <sup>(5)</sup>	509		1050	
		., ., ., .,	1.71V – 5.5V	1.71V – 5.5V	750		1836	
		$V_I = V_{CCI}$ or GND $I_O = 0$	0V	5.5V	654		1350	
Іссв	V <sub>CCB</sub> supply current		5.5V	0V	-3		36	μΑ
		V <sub>I</sub> = GND I <sub>O</sub> = 0	Floating <sup>(5)</sup>	5.5V	656		1350	
			1.8V	1.8V	1.9		3.1	
I <sub>CCA</sub> +	Supply Current -	EN = 0	2.5V	2.5V	1.9		3.1	na A
I <sub>CCB</sub>	Disable	EN - U	3.3V	3.3V	2		3.1	mA
			5V	5V	2.1		3.3	
			1.8V	1.8V	1		2.65	
		\ \ - \ \ \ .	2.5V	2.5V	1.3		2.7	^
		$V_I = V_{CCI}$	3.3V	3.3V	1.3		2.8	mA
I <sub>CCA</sub> +	Supply Current -		5V	5V	1.4		3.1	
Іссв	DC Signal		1.8V	1.8V	1.2		2.7	
		V OND	2.5V	2.5V	1.3		2.7	4
	V <sub>I</sub> =	V <sub>I</sub> = GND	3.3V	3.3V	1.3		2.8	mA
			5V	5V	1.4	,	3.1	



over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup> (2)

DADAMETED			.,	.,	Operat tempe		
P	ARAMETER	TEST CONDITIONS	V <sub>CCA</sub>	V <sub>CCB</sub>	-55°C	UNIT	
					MIN	TYP MAX	
			1.8V	1.8V	1.5	2.6	
		All channels switching with	2.5V	2.5V	1.6	2.7	] m ^
		square wave clock input; CL = 15pF, 1Mbps	3.3V	3.3V	1.6	2.8	mA
			5V	5V	1.9	3.3	
		All channels switching with square wave clock input; CL = 15pF, 50Mbps	1.8V	1.8V	9.2	12.1	
I <sub>CCA</sub> +	Supply Current - AC		2.5V	2.5V	10.8	14	
I <sub>CCB</sub>	Signal		3.3V	3.3V	12.4	16.2	mA
		, , ,	5V	5V	17.6	20.6	
			1.8V	1.8V	16.5	20.1	
		All channels switching with	2.5V	2.5V	20.2	24.7	
		square wave clock input; CL = 15pF, 100Mbps	3.3V	3.3V	24.1	29	mA
		, . ,	5V	5V	35	38	

- $V_{CCI}$  is the  $V_{CC}$  associated with the input port and referenced to GND<sub>A</sub>  $V_{CCO}$  is the  $V_{CC}$  associated with the output port and referenced to GND<sub>B</sub> (1) (2) (3)

- Tested at  $V_l = V_{T+(MAX)}$ Tested at  $V_l = V_{T-(MIN)}$ Floating is defined as a node that is both not actively driven by an external device and has leakage not exceeding 10nA (4) (5)



# 5.6 Switching Characteristics, $V_{CCA} = 1.8 \pm 0.15V$

									B-Port Supply	Voltage	e (V <sub>CCB</sub> )			
P.	ARAMETER	TEST CONDITIONS	FROM	то	TEMPERATURE	1.8	3 ± 0.15V	2.	5 ± 0.2V	3.	3 ± 0.3V	5	.0 ± 0.5V	UNIT
		CONDITIONS				MIN	TYP MAX	MIN	TYP MAX	MIN	TYP MAX	MIN	TYP MAX	
	Propagation	1Mbps all 4	А	В	-55°C to 125°C	3	7.8	3	7.8	3.1	7.9	3.1	8.4	no
t <sub>pd</sub>	delay	channels toggling	В	А	-55°C to 125°C	3	7.8	2.8	6.1	2.8	5.5	2.8	5.2	ns
	Disable time		OE	А	-55°C to 125°C	16.1	35.6	16.1	35.5	16.1	35.6	16.1	35.6	ns
t <sub>dis</sub>	Disable time		OE	В	-55°C to 125°C	17.6	42	12.6	29.1	14.7	28	10	19.3	1115
	Enable time		OE	Α	-55°C to 125°C	5.4	18.9	5.4	18.8	5.4	18.9	5.4	18.8	
t <sub>en</sub>			OE	В	-55°C to 125°C	7.9	27.5	5.5	16.3	4.5	11.8	3.8	8.4	ns
PWD	Pulse width distortion	t <sub>phi</sub> - t <sub>pih</sub>	А	В	-55°C to 125°C	0.7	1.5	0.6	1.4	0.6	1.3	0.5	1.2	ns
PWD			В	Α	-55°C to 125°C	0.7	1.5	0.6	1.4	0.6	1.3	0.5	1.2	110
	Output signal	ı	А	В	-55°C to 125°C	0.6	1.3	0.5	1.5	0.5	1.6	0.6	1.9	
t <sub>r</sub>	rise time		В	Α	-55°C to 125°C	0.5	1	0.5	1.1	0.5	1	0.5	1.1	ns
tf	Output signal		А	В	-55°C to 125°C	0.5	1.6	0.5	1.8	0.5	1.9	0.6	2.2	no
u	fall time		В	Α	-55°C to 125°C	0.5	1.4	0.5	1.5	0.5	1.4	0.5	1.4	ns
t <sub>DO</sub>	Fail-safe output delay time from input power loss				-55°C to 125°C		8.4		8.3		8.2		8	μs
t <sub>PU</sub>	time from ULVO to valid output data				-55°C to 125°C		66.8		66.8		66.8		66.9	μs

# 5.7 Switching Characteristics, $V_{CCA} = 2.5 \pm 0.2V$

									ļ	B-Port S	Supply	Voltage	(V <sub>CCB</sub>	)				
P	ARAMETER	TEST CONDITIONS	FROM	то	TEMPERATURE	1.8	1.8 ± 0.15V			2.5 ± 0.2V			3 ± 0.3\	<i>'</i>	5	.0 ± 0.5V	'	UNIT
						MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
	Propagation	1Mbps all 4	А	В	-55°C to 125°C	2.9		6.1	2.9		6.2	2.9		6.3	3		6.6	ns
<sup>L</sup> pd	delay	channels toggling	В	А	-55°C to 125°C	3		7.8	2.9		6.2	2.8		5.6	2.8		5.4	115
	Disable time		OE	А	-55°C to 125°C	11.6	-	25.2	11.6		25.2	11.6		25.2	11.6		25.2	no
t <sub>dis</sub>			OE	В	-55°C to 125°C	17.6		41.9	12.6		29.1	14.7		28	10.1		19.3	ns
	Enable time		OE	А	-55°C to 125°C	3.8		11.6	3.8		11.6	3.8		11.6	3.8		11.6	ns
Len			OE	В	-55°C to 125°C	7.9		27.5	5.5		16.3	4.5		11.8	3.8		8.4	115



# 5.7 Switching Characteristics, $V_{CCA} = 2.5 \pm 0.2V$ (continued)

									l	B-Port S	upply	Voltage	e (V <sub>CCB</sub> )	)				
P	ARAMETER	TEST CONDITIONS	FROM	то	TEMPERATURE	1.8	± 0.15V		2.	5 ± 0.2V		3.	3 ± 0.3V	1	5.0 ± 0.5V			UNIT
						MIN	TYP M	IAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
PWD	Pulse width	l+ + I	А	В	-55°C to 125°C	0.1		0.6	0.1		0.57	0.002		0.56	0.002		0.48	ns
FVVD	distortion	t <sub>phl</sub> - t <sub>plh</sub>	В	A	-55°C to 125°C	0.1		0.6	0.1		0.57	0.002		0.56	0.002		0.48	115
	Output signal rise time		А	В	-55°C to 125°C	0.6		1.3	0.5		1.4	0.5		1.7	0.6		1.9	ns
t <sub>r</sub>			В	A	-55°C to 125°C	0.5		1.1	0.5		1.2	0.5		1.2	0.5		1.1	115
tf	Output signal		А	В	-55°C to 125°C	0.5		1.6	0.5		1.7	0.5		1.8	0.5		2.1	ns
lu	fall time		В	Α	-55°C to 125°C	0.5		1.5	0.5		1.5	0.5		1.5	0.5		1.6	115
t <sub>DO</sub>	Fail-safe output delay time from input power loss				-55°C to 125°C			8.1			8.1			8			7.8	μs
t <sub>PU</sub>	time from ULVO to valid output data				-55°C to 125°C		7	71.3			71.3			71.3			71.3	μs

# 5.8 Switching Characteristics, $V_{CCA} = 3.3 \pm 0.3V$

									B-Port Supply	/ Voltag	e (V <sub>CCB</sub> )			
P	ARAMETER	TEST CONDITIONS	FROM	то	TEMPERATURE	1.8	3 ± 0.15V	2.	5 ± 0.2V	3.	3 ± 0.3V	5	.0 ± 0.5V	UNIT
						MIN	TYP MAX	MIN	TYP MAX	MIN	TYP MAX	MIN	TYP MAX	
	Propagation	1Mbps all 4	А	В	-55°C to 125°C	2.9	5.5	2.9	5.6	2.8	5.8	3	6.1	ns
t <sub>pd</sub>	delay	channels toggling	В	Α	-55°C to 125°C	3	7.9	2.9	6.3	2.8	5.7	2.8	5.5	
	Disable time		OE	A	-55°C to 125°C	13.9	25.7	13.8	25.7	13.8	25.7	13.8	25.7	ns
t <sub>dis</sub>			OE	В	-55°C to 125°C	17.6	41.9	12.6	29	14.7	28	10.1	19.3	
	. Enable time		OE	А	-55°C to 125°C	3	8.5	3.1	8.5	3.1	8.6	3	8.5	ns
t <sub>en</sub>	Enable time		OE	В	-55°C to 125°C	8	27.5	5.5	16.3	4.5	11.8	3.8	8.4	
PWD	Pulse width	l+ + l	А	В	-55°C to 125°C	0.006	0.37	0.002	0.37	0.001	0.34	0	0.36	ns
FVVD	distortion	t <sub>phi</sub> - t <sub>pih</sub>	В	A	-55°C to 125°C	0.006	0.37	0.002	0.37	0.001	0.34	0	0.36	
	Output signal		А	В	-55°C to 125°C	0.6	1.3	0.6	1.5	0.5	1.7	0.6	1.9	
t <sub>r</sub>	rise time		В	А	-55°C to 125°C	0.6	1.3	0.6	1.5	0.5	1.7	0.6	1.9	ns
tf	Output signal		А	В	-55°C to 125°C	0.5	1.7	0.5	1.7	0.5	1.8	0.6	2.1	ns
u	fall time		В	Α	-55°C to 125°C	0.5	1.7	0.5	1.7	0.5	1.7	0.5	1.6	



# 5.8 Switching Characteristics, $V_{CCA} = 3.3 \pm 0.3V$ (continued)

						B-Port Supply Voltage (V <sub>CCB</sub> )												
P	ARAMETER	TEST CONDITIONS	FROM	то	TEMPERATURE	1.8	± 0.15	0.15V 2.5 ± 0.2V		/	3.	3 ± 0.3\	/	5.0 ± 0.5V			UNIT	
	CONDITIONS					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t <sub>DO</sub>	Fail-safe output delay time from input power loss				-55°C to 125°C			8			7.9			7.9			7.7	μs
t <sub>PU</sub>	time from ULVO to valid output data				-55°C to 125°C			79.1			79.1			79.1			79.1	μs

# 5.9 Switching Characteristics, $V_{CCA} = 5.0 \pm 0.5V$

									B-Port Supp	y Voltag	e (V <sub>CCB</sub> )			
P	ARAMETER	TEST	FROM	то	TEMPERATURE	1.8	3 ± 0.15V	2.	5 ± 0.2V	3.	.3 ± 0.3V	5	.0 ± 0.5V	UNIT
						MIN	TYP MAX	MIN	TYP MAX	MIN	TYP MAX	MIN	TYP MAX	
	Propagation	1Mbps all 4	А	В	-55°C to 125°C	2.8	5.3	2.8	5.3	2.9	5.6	2.9	5.9	ns
t <sub>pd</sub>	delay	channels toggling	В	Α	-55°C to 125°C	3.1	8.3	3	6.6	2.9	6.1	2.8	5.8	3 115
	Disable time		OE	Α	-55°C to 125°C	9.4	17.7	9.4	17.7	9.4	17.7	9.4	17.7	
t <sub>dis</sub>	Disable time		OE	В	-55°C to 125°C	17.7	41.9	12.6	29.1	14.7	28	10.1	19.4	ns
	Enable time		OE	А	-55°C to 125°C	2.5	6.3	2.5	6.3	2.5	6.3	2.5	6.3	3
t <sub>en</sub>	n Enable time		OE	В	-55°C to 125°C	8	27.5	5.5	16.3	4.5	11.8	3.8	8.4	ns
DWD	Pulse width distortion	1+ + 1	А	В	-55°C to 125°C	0	0.2	0	0.3	0.003	0.4	0.011	0.7	
FVVD		t <sub>phi</sub> - t <sub>pih</sub>	В	Α	-55°C to 125°C	0	0.2	0	0.3	0.003	0.4	0.011	0.7	ns
	Output signal		А	В	-55°C to 125°C	0.6	1.3	0.5	1.5	0.5	1.7	0.6	1.9	
t <sub>r</sub>	rise time		В	А	-55°C to 125°C	0.5	1.7	0.5	1.7	0.5	1.8	0.5	1.7	ns
tf	Output signal		А	В	-55°C to 125°C	0.5	1.7	0.5	1.7	0.5	1.8	0.6	2.2	2 20
u	fall time		В	Α	-55°C to 125°C	0.5	1.7	0.5	1.7	0.5	1.8	0.6	2.2	ns
t <sub>DO</sub>	Fail-safe output delay time from input power loss				-55°C to 125°C	7.9		7.8		7.7		7.6	7.4	μs
t <sub>PU</sub>	time from ULVO to valid output data				-55°C to 125°C	98.3		98.3		98.3		98.3	96.6	β μs



# 5.10 Switching Characteristics: $T_{sk}$ , $T_{MAX}$

over operating free-air temperature range (unless otherwise noted)

					Operating free-air temperature (T <sub>A</sub> )				
PARAMETER	TEST CON	DITIONS	V <sub>CCI</sub>	V <sub>cco</sub>	-55°C	to 125°C	;	UNIT	
					MIN	TYP	MAX		
	E00/ Duty Cycle Input		1.65V - 1.95V	1.65V - 1.95V	264				
T. Mayirayını Data Data	50% Duty Cycle Input One channel switching	No Translation	2.3V - 2.7V	2.3V - 2.7V	264			Mhaa	
T <sub>MAX</sub> - Maximum Data Rate	20% of pulse > 0.7*V <sub>CCO</sub>	No Translation	3.0V - 3.6V	3.0V - 3.6V	176			Mbps	
	20% of pulse < 0.3*V <sub>CCO</sub>		4.5V - 5.5V	4.5V - 5.5V	176				
			1.65V - 1.95V	2.3V - 2.7V	264				
	500/ Duty Ovela Innyt		1.65V - 1.95V	3.0V - 3.6V	264				
T D. D.	50% Duty Cycle Input One channel switching 20% of pulse > 0.7*V <sub>CCO</sub>		1.65V - 1.95V	4.5V - 5.5V	264				
T <sub>MAX</sub> - Maximum Data Rate		Up Translation	2.3V - 2.7V	3.0V - 3.6V	264			Mbps	
	20% of pulse < 0.3*V <sub>CCO</sub>		2.3V - 2.7V	4.5V - 5.5V	220				
			3.0V - 3.6V	4.5V - 5.5V	176				
			2.3V - 2.7V	1.65V - 1.95V	285				
	500/ Duty Ovela Innyt		3.0V - 3.6V	2.3V - 2.7V	220	220			
T D. D.	50% Duty Cycle Input One channel switching	Down Translation	3.0V - 3.6V 1.65V - 1.95V		220				
T <sub>MAX</sub> - Maximum Data Rate	20% of pulse > 0.7*V <sub>CCO</sub>		4.5V - 5.5V	3.0V - 3.6V	176			Mbps	
	20% of pulse < 0.3*V <sub>CCO</sub>		4.5V - 5.5V	2.3V - 2.7V	220				
			4.5V - 5.5V	1.65V - 1.95V	220				
	Tinain a alcass b absorption		1.65V - 1.95V	1.65V - 1.95V			0.35		
4. Outside lases	Timing skew between any switching outputs on the	No. Tools delice	2.3V - 2.7V	2.3V - 2.7V			0.35		
t <sub>sk</sub> - Output skew	rising or falling edge (same	No Translation	3.0V - 3.6V	3.0V - 3.6V			0.35	ns	
	direction channels)		4.5V - 5.5V	4.5V - 5.5V			0.35		
			1.65V - 1.95V	2.3V - 2.7V			0.35		
	Tinain a alcass b absorber		1.65V - 1.95V	3.0V - 3.6V			0.35		
	Timing skew between any switching outputs on the		1.65V - 1.95V	4.5V - 5.5V		-	0.35		
t <sub>sk</sub> - Output skew	rising or falling edge (same	Up Translation	2.3V - 2.7V	3.0V - 3.6V			0.35	ns	
	direction channels)		2.3V - 2.7V	4.5V - 5.5V		0.35			
			3.0V - 3.6V	4.5V - 5.5V			0.35		



# 5.10 Switching Characteristics: T<sub>sk</sub>, T<sub>MAX</sub> (continued)

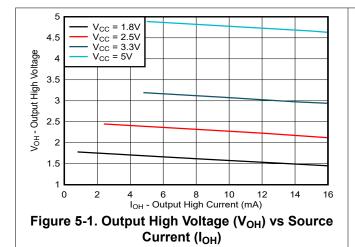
over operating free-air temperature range (unless otherwise noted)

					Operating free-air temperature (T <sub>A</sub> )			
PARAMETER	TEST CONI	DITIONS	V <sub>CCI</sub>	V <sub>cco</sub>	-55°0	UNIT		
					MIN	TYP	MAX	
	Timing skew between any switching outputs on the		2.3V - 2.7V	1.65V - 1.95V			0.35	
			3.0V - 3.6V	2.3V - 2.7V			0.35	
A Outrout alcass		Down Translation	3.0V - 3.6V	1.65V - 1.95V			0.35	
t <sub>sk</sub> - Output skew	rising or falling edge (same		4.5V - 5.5V	3.0V - 3.6V			0.35	ns
	direction channels)		4.5V - 5.5V	2.3V - 2.7V			0.35	
			4.5V - 5.5V	1.65V - 1.95V			0.35	



# **5.11 Typical Characteristics**

T<sub>A</sub> = 25°C (unless otherwise noted)



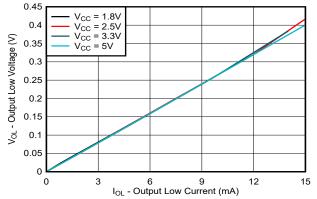


Figure 5-2. Output Low Voltage ( $V_{OL}$ ) vs Sink Current ( $I_{OL}$ )

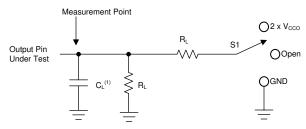


### **6 Parameter Measurement Information**

## 6.1 Load Circuit and Voltage Waveforms

Unless otherwise noted, generators supply all input pulses that have the following characteristics:

- f = 1MHz
- $Z_{O} = 50\Omega$  $\Delta t/\Delta V \le 1 \text{ns/V}$

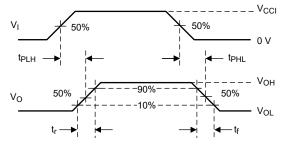


C<sub>L</sub> includes probe and jig capacitance.

Figure 6-1. Load Circuit

**Table 6-1. Load Circuit Conditions** 

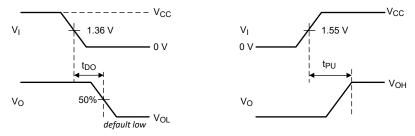
	Parameter	V <sub>cco</sub>	$R_L$	CL	S <sub>1</sub>	V <sub>TP</sub>
t <sub>pd</sub>	Propagation (delay) time	1.71V – 5.5V	10kΩ	15pF	Open	N/A
	Enable time disable time	1.71V – 2.7V	10kΩ	15pF	2 × V <sub>CCO</sub>	0.15V
en, 'dis	Enable time, disable time	3.0V - 5.5V	10kΩ	15pF	2 × V <sub>CCO</sub>	0.3V
	Enable time disable time	1.71V – 2.7V	10kΩ	15pF	GND	0.15V
t <sub>en</sub> , t <sub>dis</sub>	Enable time, disable time	3.0V - 5.5V	10kΩ	15pF	GND	0.3V



- V<sub>CCI</sub> is the supply pin associated with the input port.
- 2.  $V_{OH}$  and  $V_{OL}$  are typical output voltage levels that occur with specified  $R_L$ ,  $C_L$ , and  $S_1$

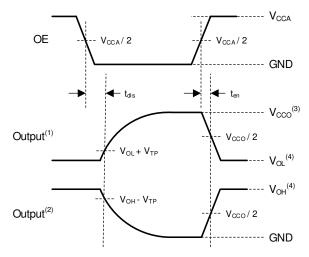
Figure 6-2. Switching Characteristics Voltage Waveforms





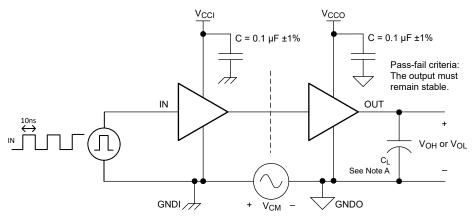
- 1.  $V_{CCI}$  is the supply pin associated with the input port.
- 2.  $V_{OH}$  and  $V_{OL}$  are typical output voltage levels that occur with specified  $R_L$ ,  $C_L$ , and  $S_1$

Figure 6-3. Default Output Delay Time & Time from UVLO to Valid Output Voltage Waveform



- 1. Output waveform on the condition that input is driven to a valid Logic Low.
- 2. Output waveform on the condition that input is driven to a valid Logic High.
- 3.  $V_{\text{CCO}}$  is the supply pin associated with the output port.
- 4.  $V_{OH}$  and  $V_{OL}$  are typical output voltage levels with specified  $R_L$ ,  $C_L$ , and  $S_1$ .

Figure 6-4. Enable Time And Disable Time



1.  $C_L = 15pF$  and includes instrumentation and fixture capacitance within  $\pm 20\%$ .

Figure 6-5. Common-Mode Transient Immunity Test Circuit



## 7 Detailed Description

#### 7.1 Overview

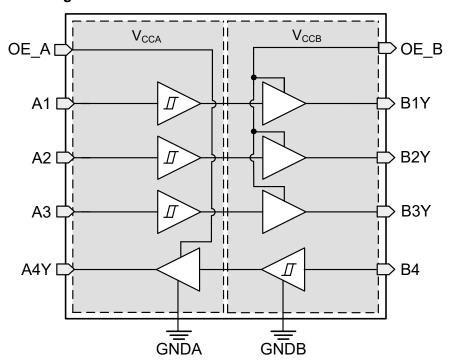
The TXG8041-EP is a 4-bit ground-level translator that uses two individually configurable power-supply rails which allows it to translate across two different power domains. The device is operational with  $V_{CCA}$  and  $V_{CCB}$  supplies as low as 1.71V and as high as 5.5V. The A port is designed to track  $V_{CCA}$  and the B port is designed to track  $V_{CCB}$ . In addition to I/O level shifting, this translator can support a difference of -80V to +80V between GNDA and GNDB.  $V_{CCA}$  is referenced to GNDA and  $V_{CCB}$  is referenced to GNDB.

The TXG8041-EP is designed for asynchronous communication between data buses, and transmits data with fixed direction from the A bus to the B bus on some channels and from the B bus to the A bus on the remaining channels. The output-enable input (OE) is used to disable the outputs so the buses are effectively isolated. The OE\_A pin is referenced to  $V_{CCA}$  and OE\_B pin is referenced to  $V_{CCB}$ . The OE pin can be left floating or externally pulled down to ground to keep the translator outputs in a high-impedance state during power-up or power-down.

The  $V_{CC}$  disconnect feature ensures that if  $V_{CC}$  is disconnected with the complementary supply within recommended operating conditions, outputs are disabled and set to the high-impedance state while the supply current is maintained. The  $I_{off-float}$  circuitry ensures that no excessive current is drawn from or sourced into an input or output while the supply is floating.

Glitch-free power supply sequencing allows either supply rail to be powered on or off in any order while providing robust power sequencing performance.

#### 7.2 Functional Block Diagram



**TXG8041-EP Functional Block Diagram** 



#### 7.3 Feature Description

#### 7.3.1 CMOS Schmitt-Trigger Inputs with Integrated Pulldowns

Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the Section 5.5. The worst case resistance is calculated with the maximum input voltage, given in the Section 5.1, and the maximum input leakage current, given in the Section 5.5, using ohm's law (R = V ÷ I).

The Schmitt-trigger input architecture provides hysteresis as defined by  $\Delta V_T$  in the Section 5.5, which makes this device extremely tolerant to slow or noisy inputs. Driving the inputs slowly will increase dynamic current consumption of the device. See Understanding Schmitt Triggers for additional information regarding Schmitttrigger inputs.

#### 7.3.1.1 Inputs with Integrated Static Pull-Down Resistors

This device has  $5M\Omega$  typical integrated weak pull-downs for each input. This feature allows all inputs to be left floating without the concern for unstable outputs or increased current consumption. This also helps to reduce external component count for applications where not all channels are used or need to be fixed low. If an external pull-up is required, it should be no larger than  $1M\Omega$  to avoid contention with the  $5M\Omega$  internal pull-down.

#### 7.3.2 Balanced High-Drive CMOS Push-Pull Outputs

A balanced output allows the device to sink and source similar currents. The high drive capability of this device creates fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. Section 5.1 defines the electrical and thermal limits that must be followed at all times.

#### 7.3.3 V<sub>CC</sub> Disconnect

The outputs for this device are disabled and enter a high-impedance state when either supply is left floating (disconnected), and with the complementary supply within recommended operating conditions. It is recommended that the inputs are kept low before floating (disconnecting) either supply.

The I<sub>CCx(floating)</sub> in the Section 5.5 specifies the maximum supply current. The I<sub>off(float)</sub> in the Section 5.5 specifies the maximum leakage into or out of any input or output pin on the device.

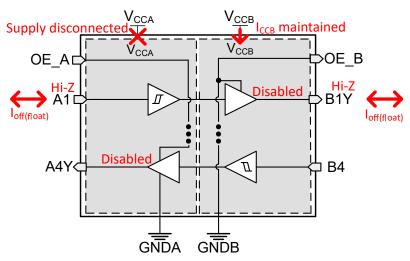


Figure 7-1. V<sub>CC</sub> Disconnect Feature

#### 7.3.4 Over-Voltage Tolerant Inputs

Input signals to this device can be driven above the supply voltage so long as they remain below the maximum input voltage value specified in the Section 5.3.



### 7.3.5 Glitch-Free Power Supply Sequencing

Either supply rail may be powered on or off in any order without producing a glitch on the inputs or outputs (that is, where the output erroneously transitions to  $V_{CC}$  when it should be held low or vice versa). Glitches of this nature can be misinterpreted by a peripheral as a valid data bit, which could trigger a false device reset of the peripheral, a false device configuration of the peripheral, or even a false data initialization by the peripheral.

#### 7.3.6 Negative Clamping Diodes

Figure 7-2 depicts the inputs and outputs to this device that have negative clamping diodes.

#### **CAUTION**

Voltages beyond the values specified in the Section 5.1 table can cause damage to the device. The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

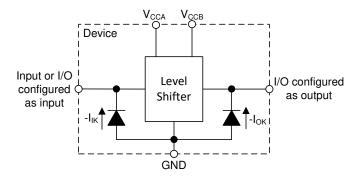


Figure 7-2. Electrical Placement of Clamping Diodes for Each Input and Output

#### 7.3.7 Fully Configurable Dual-Rail Design

The  $V_{CCA}$  and  $V_{CCB}$  pins can be supplied at any voltage from 1.71V to 5.5V, making the device suitable for translating between any of the voltage nodes (1.8V, 2.5V, 3.3V, and 5.0V).

#### 7.3.8 Supports High-Speed Translation

The TXG8041-EP device can support high data-rate applications. The translated signal data rate can be greater than 250Mbps when the signal is translated from 1.71V to 5.5V.

Voltage:



### 7.3.9 AC Noise Rejection

TXG8041-EP supports I/O voltage translation in environments with noisy grounds. The plot below illustrates the amount of noise that GNDA and GNDB can reject in terms peak-to-peak voltage over frequency without disrupting communication between two systems. As an example, Figure 7-4 below shows GNDA with a ground bounce of 2V<sub>PP</sub> at 10kHz but still effectively translating 5V to 2.5V without any degradation.

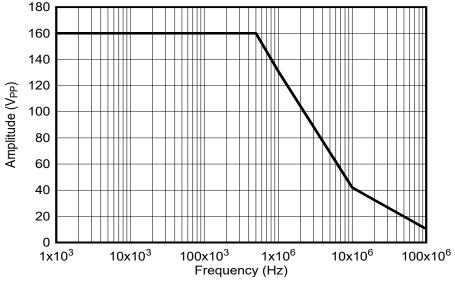


Figure 7-3. AC Noise Rejection Plot

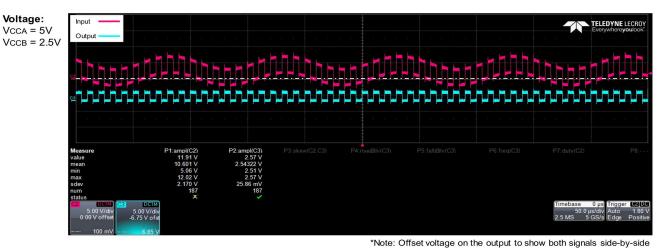


Figure 7-4. Waveform showing 5V to 2.5V I/O translation with AC Ground Noise of 2V<sub>PP</sub> at 10kHz



### 7.4 Device Functional Modes

**Table 7-1. Function Table** 

Power	Supply	Control Inputs	Port Status				
VCCI	vcco	OE	Input	Output			
PU	PU	Н	Н	Н			
PU	PU	Н	L	L			
PU	PU	L or Open	X	Hi-Z			
PU	PU	Н	Open	L			
PD	PU	Н	X	L			
X	PU	L or Open	X	High-Z			
Х	PU	Н	X	L			
X	PD	X	X	Undetermined			

1. In the table above: PU = Powered Up; PD = Powered Down; X = Irrelevant; H = High Level; L = Low Level; Open = Floating



# 8 Application and Implementation

#### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

# 8.1 Application Information

The TXG8041-EP is used for level translation, enabling communication between devices or systems operating at different interface and ground voltages. The TXG8041-EP is ideal for use in applications where a push-pull driver is connected to the data inputs. Figure 8-1 is an example of two systems that translate from 1.8V to 3.3V across a SPI interface while also seeing a ground shift of -3V on GNDB while GNDA is at 0V. The ground shift of 3V is from the noisy power ground of the Digital-to-Analog Converter (DAC).

### 8.2 Typical Application

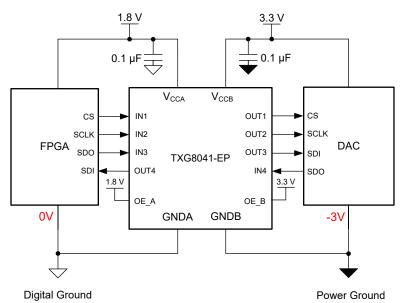


Figure 8-1. TXG8041-EP in Avionics

## 8.2.1 Design Requirements

Use the parameters listed in Table 8-1 for this design example.

Table 8-1. Design Parameters

DESIGN PARAMETERS	EXAMPLE VALUES
Input voltage range	1.71V to 5.5V
Output voltage range	1.71V to 5.5V

#### 8.2.2 Detailed Design Procedure

To begin the design process, determine the following:

- Input voltage range
  - Use the supply voltage of the device that is driving the TXG8041-EP to determine the input voltage range.
     For a valid logic-high, the value must exceed the positive-going input-threshold voltage (V<sub>T+</sub>) of the input



port. For a valid logic low the value must be less than the negative-going input-threshold voltage  $(V_{T-})$  of the input port.

- Output voltage range
  - Use the supply voltage of the device that the TXG8041-EP is driving to determine the output voltage range.

### 8.2.3 Application Curves

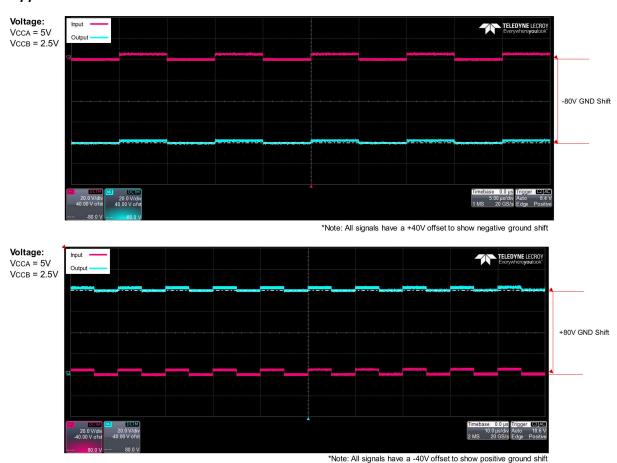


Figure 8-2. Waveform showing -80V (top) and +80V (bottom) Ground Shift with 5V to 2.5V I/O Translation



#### 8.3 Power Supply Recommendations

Always apply a ground reference to the GND pins first. This device is designed for glitch free power sequencing without any supply sequencing requirements such as ramp order or ramp rate. Please make sure the difference between  $V_{CC}$  and GND remains at 6.5V max at all times.

#### 8.4 Layout

#### 8.4.1 Layout Guidelines

To ensure reliability of the device, following common printed-circuit board layout guidelines are recommended:

- Use bypass capacitors on the power supply pins and place them as close to the device as possible. A 0.1µF capacitor is recommended, but transient performance can be improved by having 1µF and 0.1µF capacitors in parallel as bypass capacitors.
- The high drive capability of this device creates fast edges into light loads so routing and load conditions should be considered to prevent ringing.
- A 0.1µF capacitor can be added between GNDA and GNDB to improve performances of CMTI.

#### 8.4.2 Layout Example

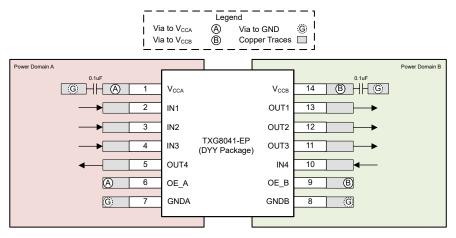


Figure 8-3. DYY Layout Example



# 9 Device and Documentation Support

# 9.1 Device Support

#### 9.1.1 Regulatory Requirements

No statutory or regulatory requirements apply to this device.

There are no special characteristics for this product.

#### 9.2 Documentation Support

#### 9.2.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, Understanding Schmitt Triggers application report
- Texas Instruments, CMOS Power Consumption and Cpd Calculation application report

#### 9.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 9.4 Support Resources

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

#### 9.5 Trademarks

TI E2E<sup>™</sup> is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

#### 9.6 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### 9.7 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

# 10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

DATE	REVISION	NOTES
June 2025	*	Initial Release

# 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

www.ti.com 19-Jun-2025

#### PACKAGING INFORMATION

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	RoHS (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
PTXG8041MDYYREP	Active	Preproduction	SOT-23-THIN (DYY)   14	2500   LARGE T&R	-	Call TI	Call TI	-40 to 125	

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

- (3) RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.
- (4) Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.
- (5) MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.
- (6) Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

#### OTHER QUALIFIED VERSIONS OF TXG8041-EP:

Catalog: TXG8041

<sup>(2)</sup> Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

# PACKAGE OPTION ADDENDUM

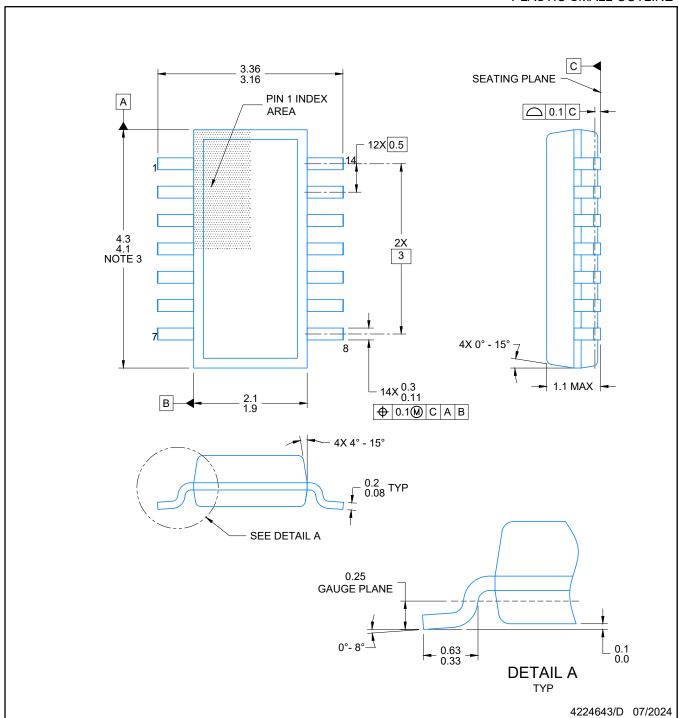
www.ti.com 19-Jun-2025

• Automotive : TXG8041-Q1

NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Automotive Q100 devices qualified for high-reliability automotive applications targeting zero defects

PLASTIC SMALL OUTLINE

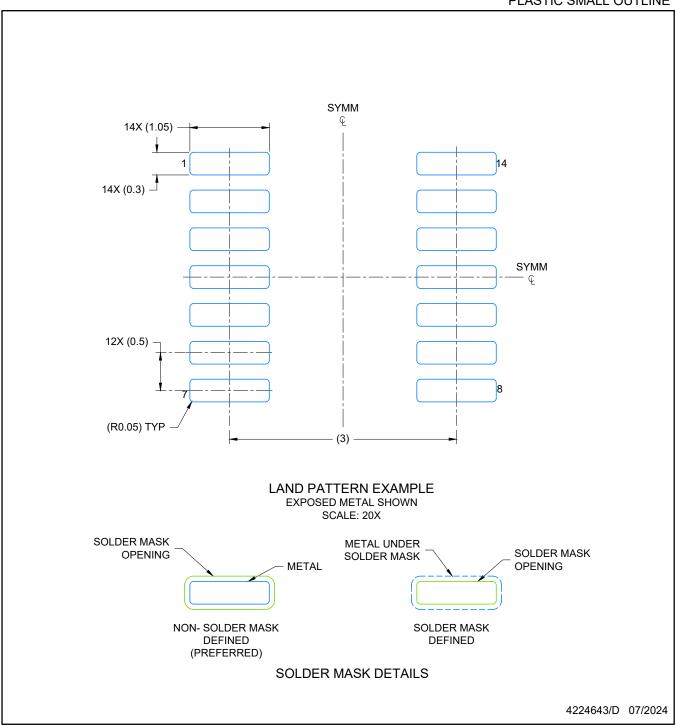


#### NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per side
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
- 5. Reference JEDEC Registration MO-345, Variation AB



PLASTIC SMALL OUTLINE

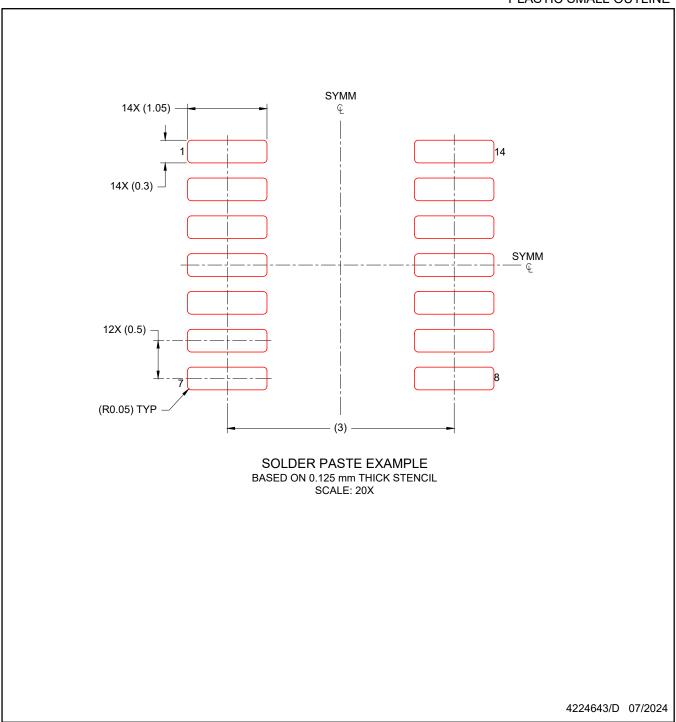


NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



PLASTIC SMALL OUTLINE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



#### IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2025. Texas Instruments Incorporated